

Features

- Excellent dynamic characteristics
- Fast turn-on and high di/dt
- Low switching losses

Typical Applications

- Design for inverter supply application

品名: FH2900TN

 $I_{T(AV)}$ 2900A V_{DRM} 2000~3000V V_{RRM} 1000~2500V t_q 20-75 μ s

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		$T_j(^{\circ}\text{C})$	VALUE			UNIT
					Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled	$T_c=55^{\circ}\text{C}$	125			2900	A
V_{DRM}	Repetitive peak off-state voltage	$t_p=10\text{ms}$		125	2000		3000	V
V_{RRM}	Repetitive peak reverse voltage				1000		2500	
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}		125			200	mA
I_{TSM}	Surge on-state current	10ms half sine wave		125			30	kA
I^2t	I^2t for fusing coordination	$V_R=0.6V_{RRM}$					4500	
V_{TO}	Threshold voltage			125			1.27	V
r_T	On-state slope resistance						0.15	
V_{TM}	Peak on-state voltage	$I_{TM}=5000\text{A}$, $F=40\text{kN}$	$20\mu\text{s} \leq t_q \leq 45\mu\text{s}$	25			2.80	V
			$46\mu\text{s} \leq t_q \leq 60\mu\text{s}$				2.60	V
			$61\mu\text{s} \leq t_q \leq 75\mu\text{s}$				2.40	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$		125			1000	$\text{V}/\mu\text{s}$
di/dt	Critical rate of rise of on-state current (Non-repetitive)	$V_{DM}=67\%V_{DRM}$, Gate pulse $t_r \leq 0.5\mu\text{s}$ $I_{GM}=1.5\text{A}$		125			1500	$\text{A}/\mu\text{s}$
Q_{rr}	Recovery charge	$I_{TM}=2000\text{A}$, $t_p=4000\mu\text{s}$, $di/dt=-20\text{A}/\mu\text{s}$, $V_R=100\text{V}$		125		1300		μC
t_q	Circuit commutated turn-off time	$I_{TM}=2000\text{A}$, $t_p=4000\mu\text{s}$, $V_R=100\text{V}$ $dv/dt=30\text{V}/\mu\text{s}$, $di/dt=-20\text{A}/\mu\text{s}$		125	25		75	μs
I_{GT}	Gate trigger current	$V_A=12\text{V}$, $I_A=1\text{A}$		25	40		250	mA
V_{GT}	Gate trigger voltage		0.9			3.0	V	
I_H	Holding current		20			1000	mA	
I_L	Latching current					1500	mA	
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$		125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	DC, double side cooled Clamping force 40kN					0.010	$^{\circ}\text{C}/\text{W}$
$R_{th(c-h)}$	Thermal resistance case to heatsink						0.003	
F_m	Mounting force				35		47	kN
T_{vj}	Junction temperature				-40		125	$^{\circ}\text{C}$
T_{stg}	Stored temperature				-40		140	$^{\circ}\text{C}$
W_t	Weight					1100		g
Outline	P17							

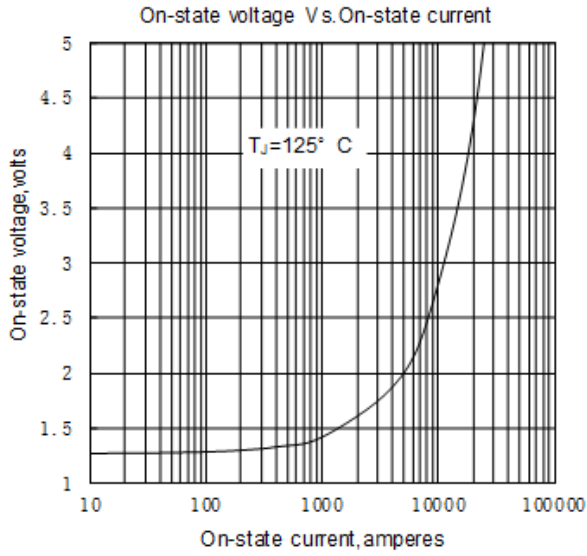


Fig. 1

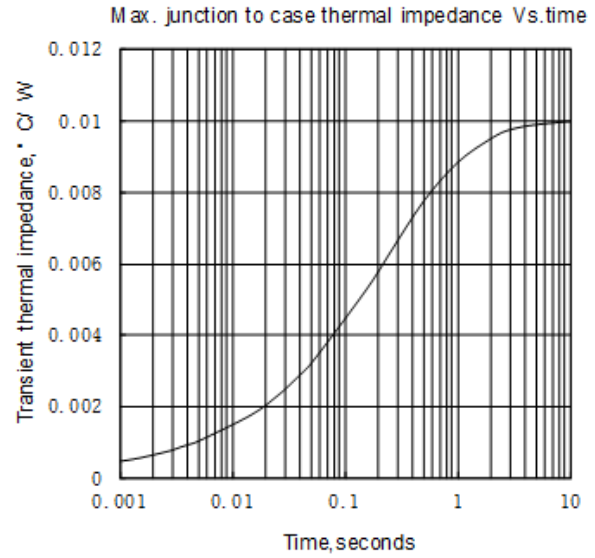


Fig. 2

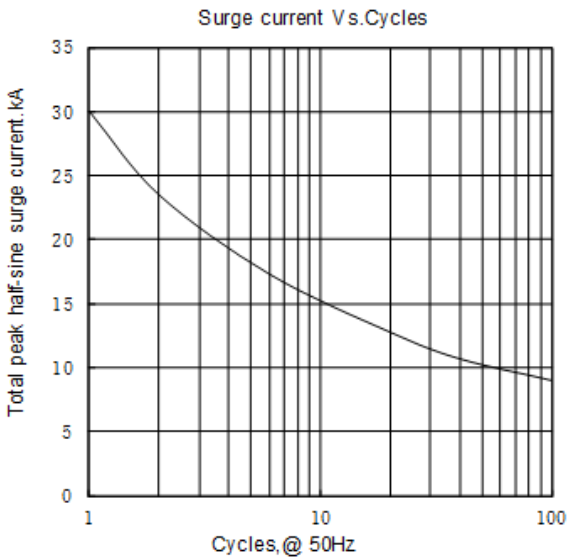


Fig. 3

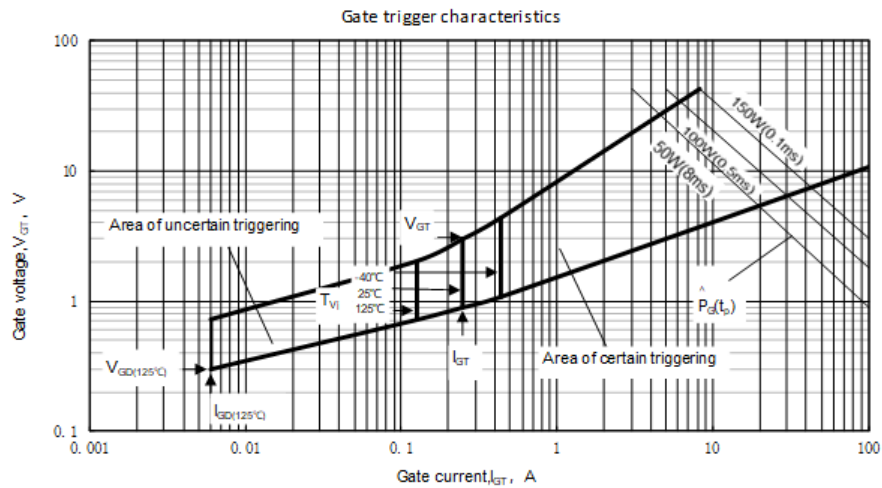
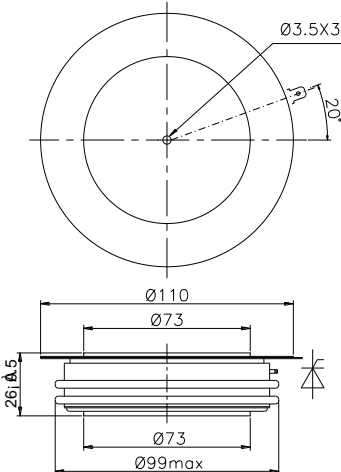


Fig. 4



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